● PRINTER RUSH ●

(PTO ASSISTANCE)

2nd request

Application :	10/078056	**Examiner :**	Lee	**GAU :**	2881
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[RUSH] **MESSAGE:** Renumbered claims 31, 32, 33 (original claims 33, 34, 35 depend on renumbered claim 34 (original claim 36).

Thank you.

[XRUSH] **RESPONSE:** OK to change renumbered claims 31, 32, 33 To depend on renumbered claim 34

INITIALS: CF

NOTE: This form will be included as part of the official USPTO record, with the Response document coded as XRUSH.

REV 10/04

31 ~~33.~~ (Previously Presented) The system of claim ~~36~~ 34, wherein electric charges drawn across the semiconductor layer is greater near the first surface of the semiconductor layer adjacent to the charge-collection layer relative to the second surface.

32 ~~34.~~ (Previously Presented) The digital radiography system of claim ~~36~~ 34, wherein the flat panel imager is a TFT-based imager.

33 ~~35.~~ (Previously Presented) The digital radiography system of claim ~~36~~ 34, wherein the flat panel imager is a CCD-based imager.

34 ~~36.~~ (Previously Presented) A digital radiography system, comprising:

an x-ray source to transmit x-rays;

a flat panel imager to receive the x-rays and to produce a digitized image, comprising:

a semiconductor layer disposed above a charge-collection layer;

a bias electrode layer disposed above the semiconductor layer, the bias electrode to generate an electric field within the semiconductor layer; and

a casing that holds the flat panel imager together, wherein the casing forms an aperture window to receive the x-rays; and

a display system connected to the flat panel imager, the display system to display the digitized image, wherein the semiconductor layer has a first surface adjacent to the charge-collection layer and a second surface adjacent to the bias electrode, and wherein the flat panel imager is configured such that x-rays traverse the charge-collection layer before propagating through the semiconductor layer.